

[illegible]

FIG. 2

Diagram illustrating a cross-sectional view of a semiconductor device structure. The structure features a central vertical element (3) with a central core (12) and a central layer (12a). This central element is flanked by two horizontal blocks (5 and 7), each with a top layer (2a) and a bottom layer (11). The central element is surrounded by a material (4). The angle between the central element and the surrounding material is labeled "ANGLE : LARGE". Dimensions are indicated at the bottom: "LAND WIDTH : SMALL", "LAND AREA, RADIUS : SMALL", and "LAND DIAMETER : SMALL".

FIG.3

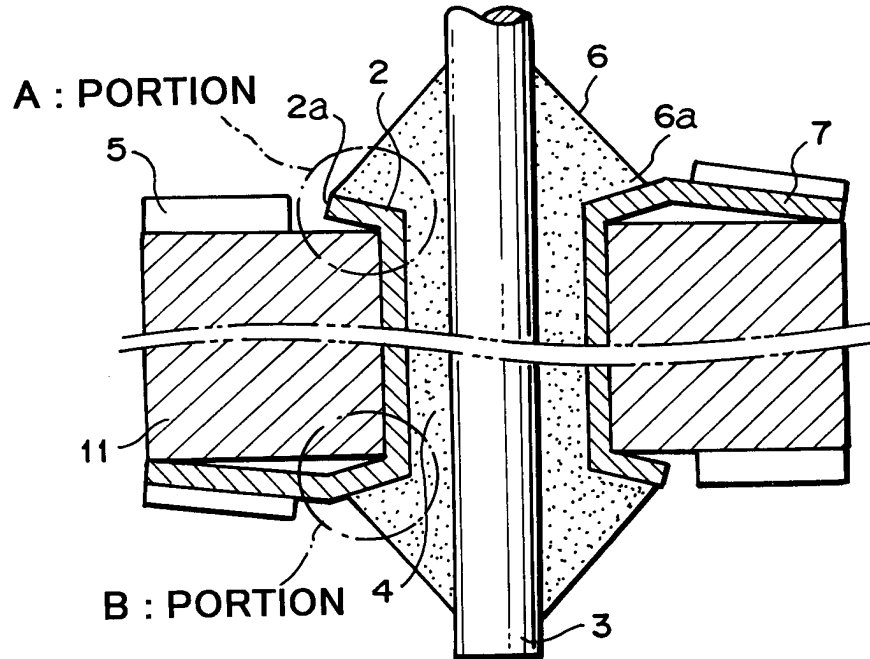


FIG.4

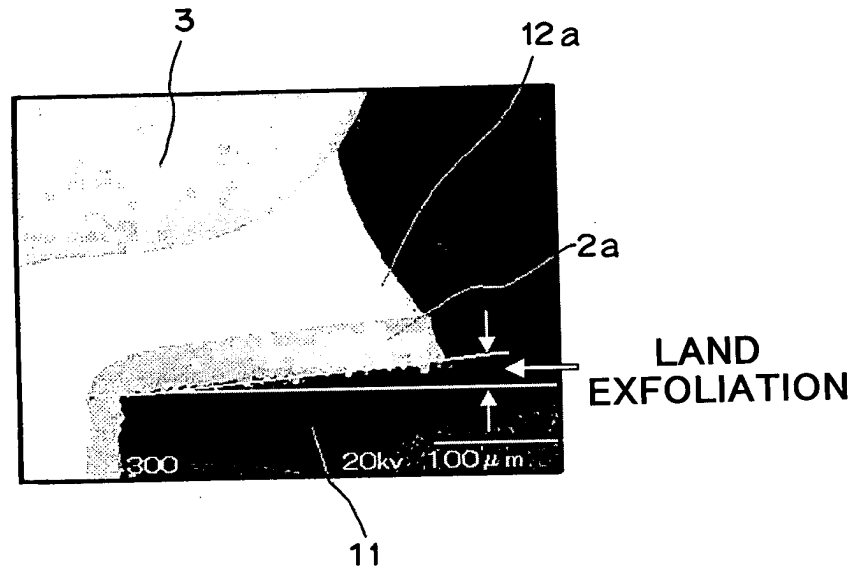


FIG.5

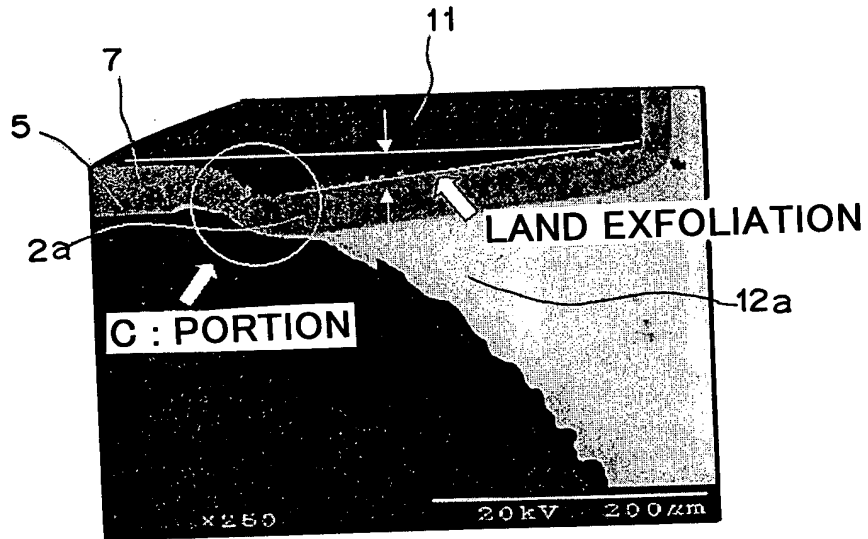


FIG.6

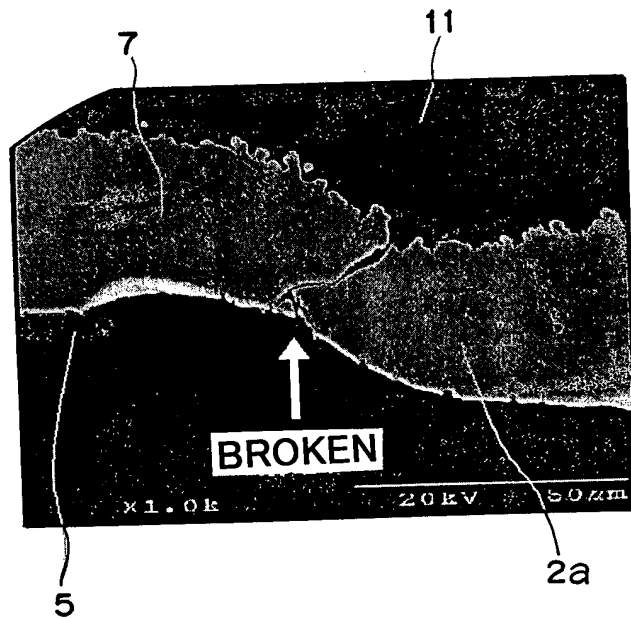


FIG. 5

FIG.7

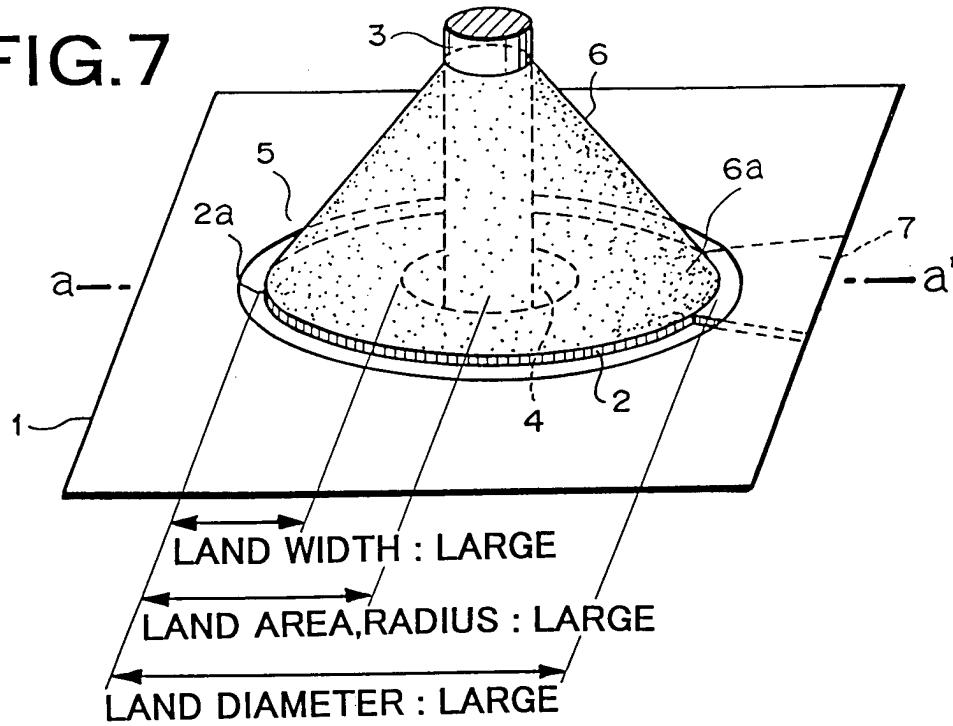
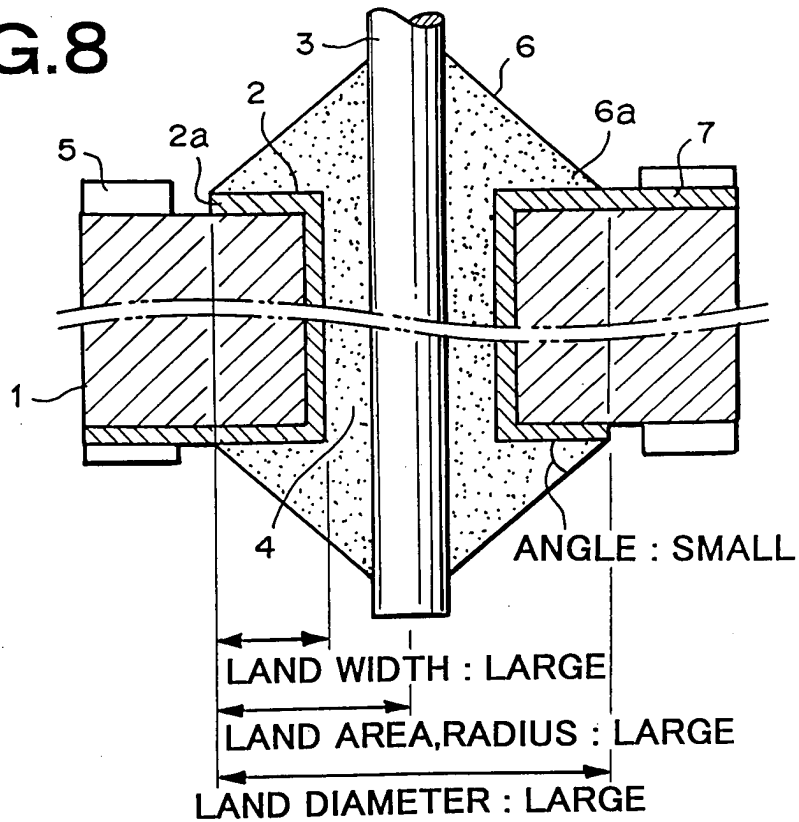


FIG.8



09985727 110601

FIG. 9

(LAND DIAMETER Y : EXAMPLE, LAND DIAMETER X : COMPARISON EXAMPLE)

EXAMPLE COMPARISON EXAMPLE	THROUGH HOLE DIAMETER Z(mm)	LAND DIAMETER X (mm)	LAND DIAMETER Y (mm)	X LAND WIDTH (X-Z)/2	Y LAND WIDTH (X-Y)/2	INCIDENCE OF X LAND EXFOLIATION(%)	INCIDENCE OF Y LAND EXFOLIATION(%)
EXAMPLE 1 COMPARISON EXAMPLE 1	0.6	1.1	1.4	0.25	0.4	31.3	0
EXAMPLE 2 COMPARISON EXAMPLE 2	0.8	1.3	1.6	0.25	0.4	21	4
EXAMPLE 3 COMPARISON EXAMPLE 3	0.9	1.35	1.7	0.225	0.4	25	0
EXAMPLE 4 COMPARISON EXAMPLE 4	0.9	1.35	1.7	0.225	0.4	69.2	0
EXAMPLE 5 COMPARISON EXAMPLE 5	1	1.6	1.9	0.3	0.45	33	0
EXAMPLE 6 COMPARISON EXAMPLE 6	1.5	2.2	2.5	0.35	0.5	21	0
EXAMPLE 7 COMPARISON EXAMPLE 7	1.7	2.4	2.7	0.35	0.5	37.5	0
EXAMPLE 8 COMPARISON EXAMPLE 8	0.8	1.4	1.7	0.3	0.45	84	6
EXAMPLE 9 COMPARISON EXAMPLE 9	1	1.6	1.9	0.3	0.45	56	6

FIG.10A

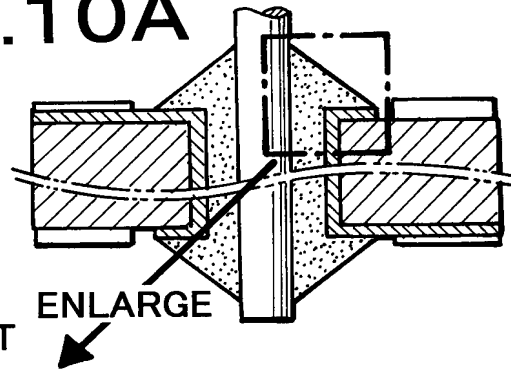


FIG.10B

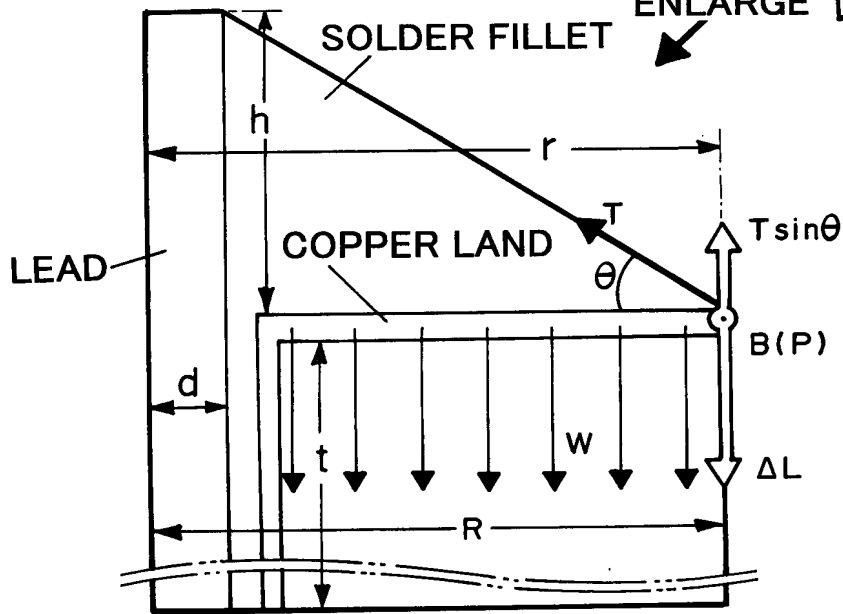
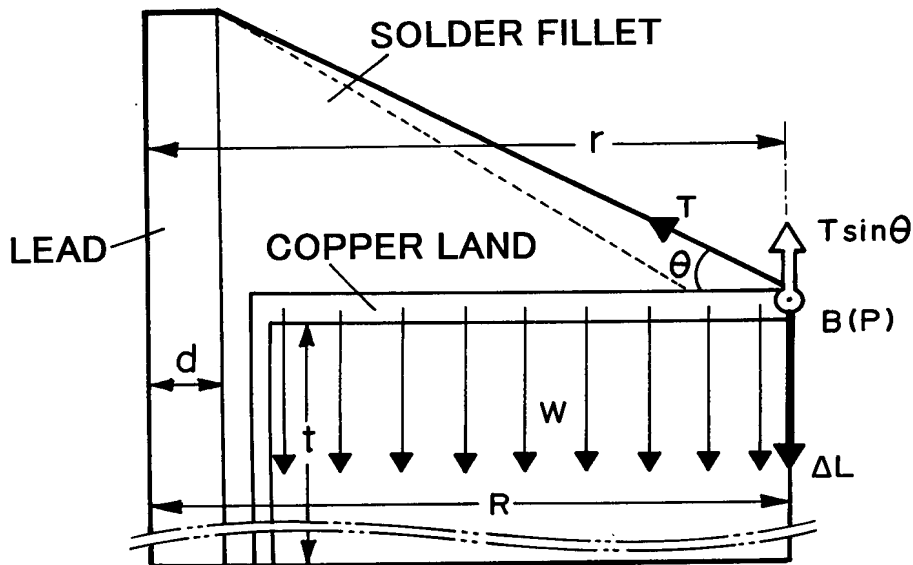
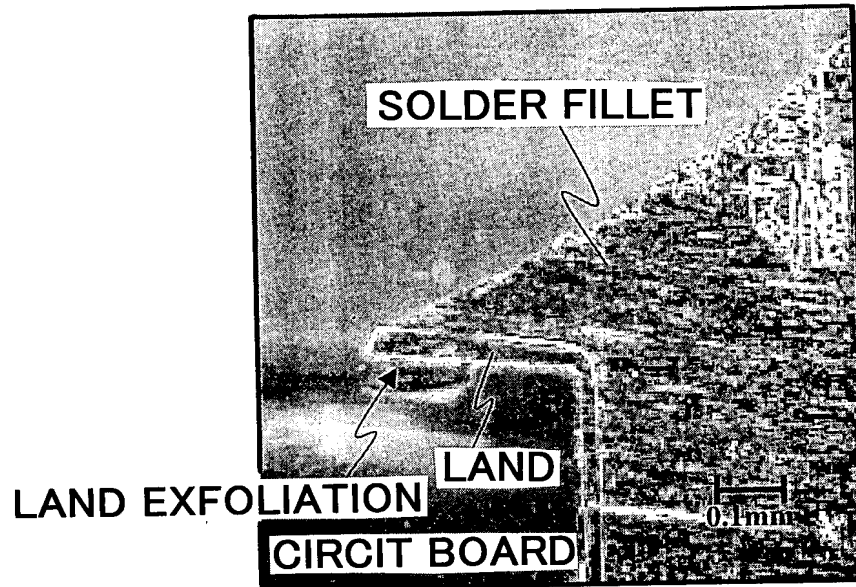


FIG.10C



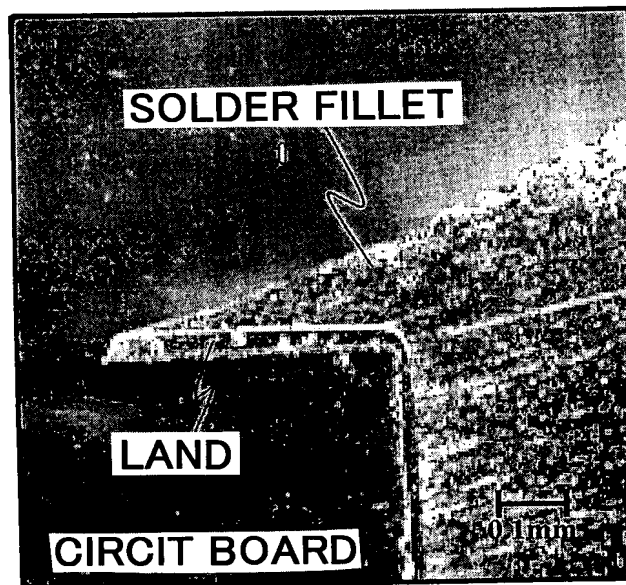
0995727-110601

FIG.11



LAND RADIUS : 0.25mm

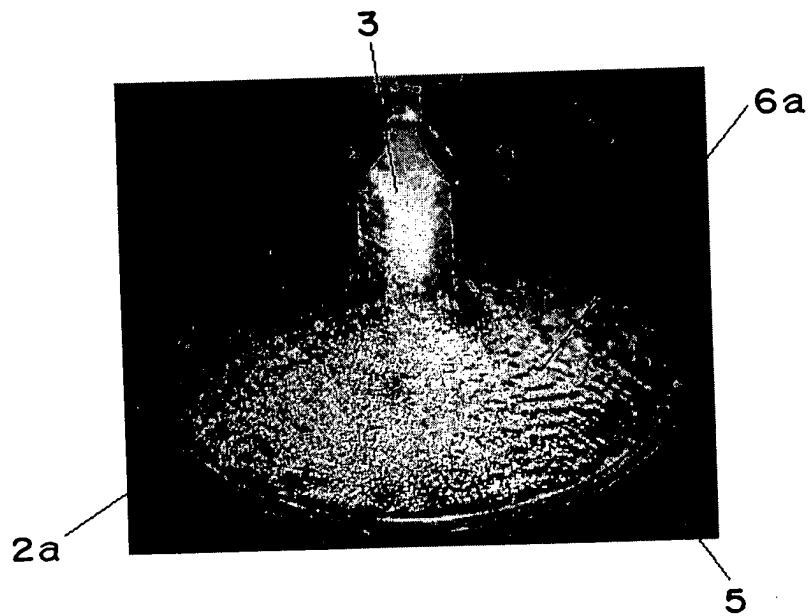
FIG.12



LAND RADIUS : 0.4mm

09985727.110601

FIG. 13



09985727.110601

FIG. 14

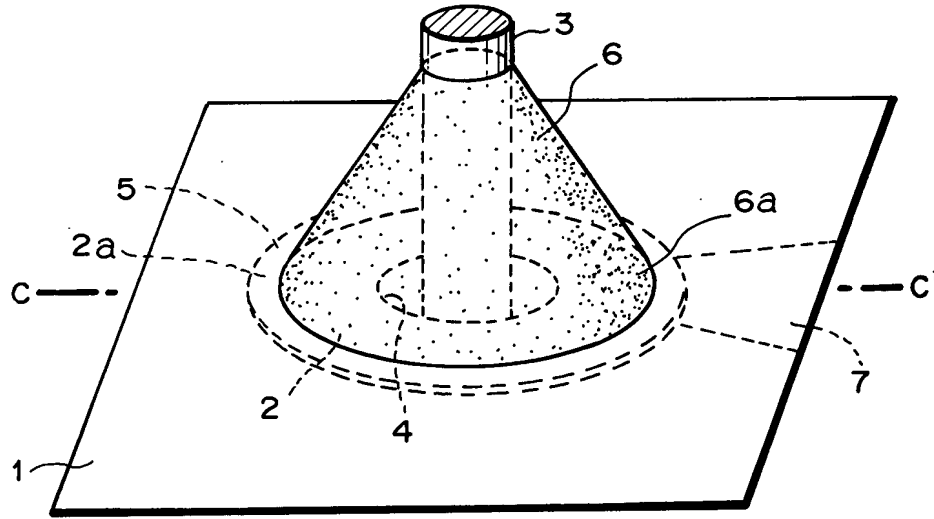


FIG. 15

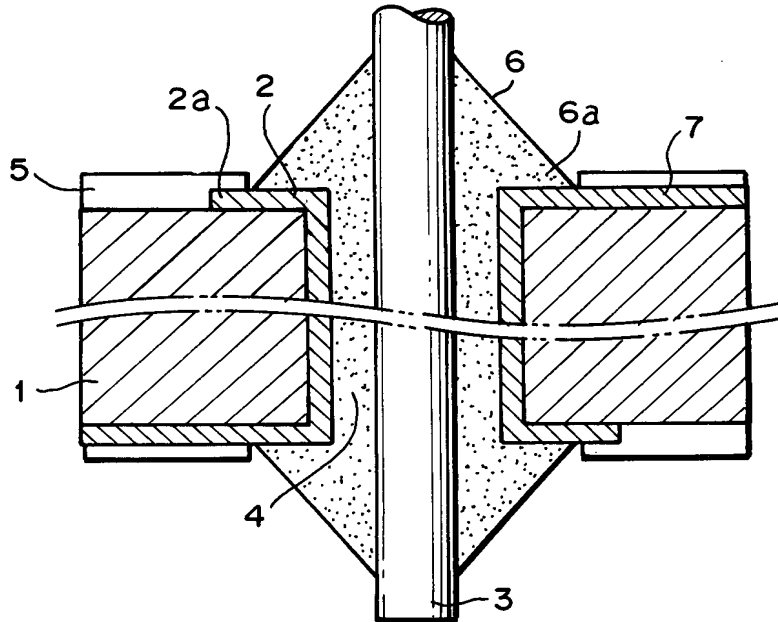


FIG. 14